TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH373FK

Octal D-Type Latch with 3-State Output

The TC7MH373FK is an advanced high speed CMOS octal latch with 3-state output fabricated with silicon gate $\rm C^2MOS$ technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while marinating the CMOS low power dissipation.

This 8 bit D-type latch is controlled by a latch enable input (LE) and an output enable input (\overline{OE}).

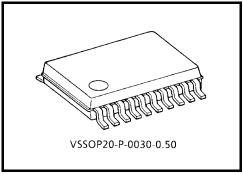
When the $\overline{\text{OE}}$ input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures the 0 to 5.5~V can be applied to the input pins can be used to interface 5~V to 3~V systems and two supply systems such as battery back up.

This circuit prevents destruction due to mismatched supply and input voltages.

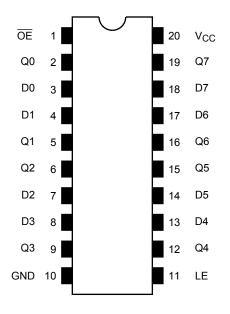
Features

- High speed: $t_{pd} = 5.0 \text{ ns (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range: $V_{CC (opr)} = 2 \sim 5.5 \text{ V}$
- Low noise: $V_{OLP} = 0.8 \text{ (max)}$
- Pin and function compatible with 74ALS373

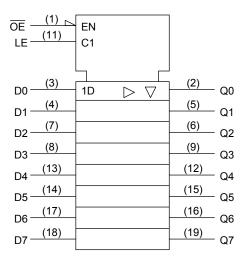


Weight: 0.03 g (typ.)

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

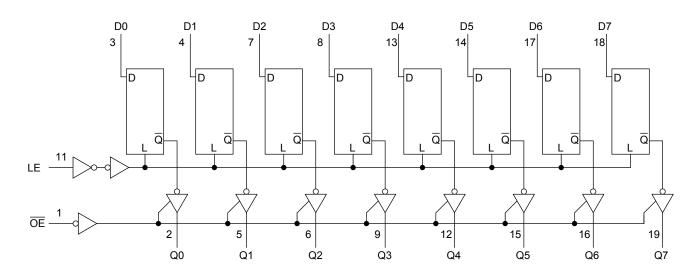
	Inputs					
ŌĒ	LE	D	Outputs			
Н	Х	Х	Z			
L	L	Х	Qn			
L	Н	L	L			
L	Н	Н	Н			

X: Don't care

Z: High impedance

 Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram





Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	I _{CC}	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	٧
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100~(V_{CC}=3.3\pm0.3~V)$	ns/V
input rise and rail time	uuuv	$0~20~(V_{CC} = 5 \pm 0.5~V)$	113/ V

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics		Cumbal	Symbol Test Condition			-	Ta = 25°0		Ta = -40~85°C		Unit
Cilarac	ciensucs	Syllibol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
					2.0	1.50	_	_	1.50	_	
High level		V _{IH}	_		3.0~5.5	V _{CC} × 0.7	_	ı	V _{CC} × 0.7	١	V
Input voltage					2.0		_	0.50	_	0.50	V
	Low level	V _{IL}		_	3.0~5.5		_	V _{CC} × 0.3	_	V _{CC} × 0.3	
				Ι _{ΟΗ} = -50 μΑ	2.0	1.9	2.0		1.9		
		Vон	V _{IN} = V _{IH} or V _{IL}		3.0	2.9	3.0		2.9		
	High level				4.5	4.4	4.5		4.4		
Output				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_		2.48		
				$I_{OH} = -8 \text{ mA}$	4.5	3.94		_	3.80	_	
voltage				I _{OL} = 50 μA	2.0	_	0	0.1	—	0.1	
					3.0	_	0	0.1	—	0.1	
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}		4.5	_	0	0.1	—	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	—	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5	_	—	0.36	_	0.44	
3-state output	off-state current	I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		5.5		_	±0.25	_	±2.50	μА
Input leakage	current	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5		_	±0.1	_	±1.0	μА
Quiescent sup	ply current	Icc	V _{IN} = V _{CC} or GND		5.5	_	_	4.0	_	40.0	μΑ

Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Cymbol	Test Condition		Ta = 25°C		Ta = -40~85°C	Unit	
Characteristics			V _{CC} (V)	Тур.	Limit	Limit	Offic	
Minimum pulse width	t a.n	_	3.3 ± 0.3	_	5.0	5.0	ns	
(LE)	t _{w (H)}		5.0 ± 0.5	_	5.0	5.0	113	
Minimum set-up time	ts		3.3 ± 0.3	_	4.0	4.0	ns	
		_	5.0 ± 0.5	_	4.0	4.0	115	
Minimum hold time	t _h		3.3 ± 0.3	_	1.0	1.0	ns	
		_	5.0 ± 0.5	_	1.0	1.0	115	

AC Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	ndition		Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
			3.3 ± 0.3	15	_	7.0	11.0	1.0	13.0	ns
Propagation delay time	t _{pLH}		3.3 ± 0.3	50	_	9.5	14.5	1.0	16.5	
(LE-Q)	tpHL	_	5.0 ± 0.5	15	_	4.9	7.2	1.0	8.5	115
			5.0 ± 0.5	50	_	6.4	9.2	1.0	10.5	
			3.3 ± 0.3	15	_	7.3	11.4	1.0	13.5	
Propagation delay time	t _{pLH}		3.3 ± 0.3	50	_	9.8	14.9	1.0	17.0	no
(D-Q)	t _{pHL}	_	5.0 ± 0.5	15	_	5.0	7.2	1.0	8.5	ns
			5.0 ± 0.5	50	_	6.5	9.2	1.0	10.5	
	t _{pZL} t _{pZH}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15	_	7.3	11.4	1.0	13.5	ns ns
3-state output enable time				50	_	9.8	14.9	1.0	17.0	
3-state output enable time			5.0 ± 0.5	15	_	5.5	8.1	1.0	9.5	
				50	_	7.0	10.1	1.0	11.5	
3-state output disable time	t _{pLZ}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	50	_	9.5	13.2	1.0	15.0	ns
3-state output disable time	t_{pHZ}		5.0 ± 0.5	50	_	6.5	9.2	1.0	10.5	115
Output to output skew	t _{osLH}	(Note 1)	3.3 ± 0.3	50	_	_	1.5	_	1.5	no
Output to output skew	t _{osHL}	(Note 1)	5.0 ± 0.5	50	_	_	1.0	_	1.0	ns
Input capacitance	C _{IN}	_			_	4	10	_	10	pF
Bus input capacitance	C _{OUT}	-	_		_	6	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note 2)	_	27	_	_	_	pF

Note 1: This parameter is guaranteed by design.

 $t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per latch)}$

And the total CPD when n pcs of latch operate can be gained by the following equation:

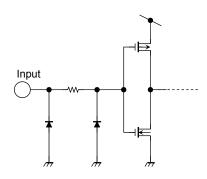
 C_{PD} (total) = 14 + 13 · n

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Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		- Unit
Citalacteristics	Syllibol	rest condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.5	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.5	-0.8	V
Minimum high level dynamic input voltage V_{IH}	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

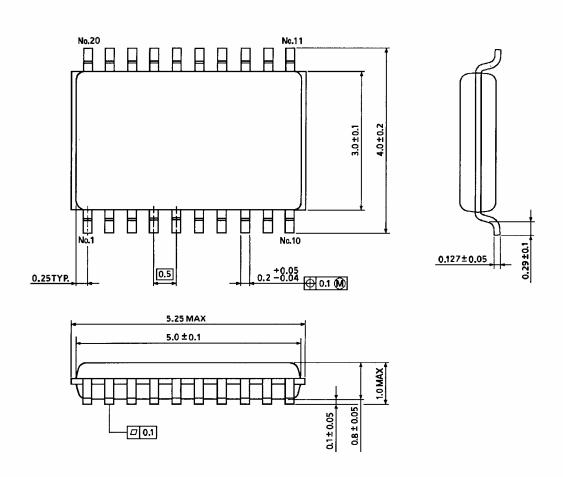
Input Equivalent Circuit



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Package Dimensions



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Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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